2SA1359

Rev.E Mar.-2016

蓝箭电子 BLUE ROCKET ELECTRONICS

DATA SHEET

/ Descriptions

TO-126F PNP Silicon PNP transistor in a TO-126F Plastic Package.

/ Features

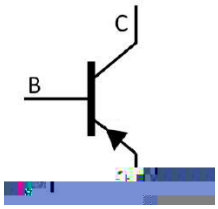
2SC3422

Good linearity of h_{FE} ,complementary to 2SC3422.

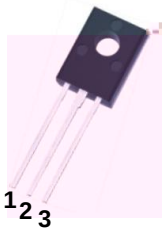
/ Applications

Audio frequency power amplifier and low speed switching applications.

/ Equivalent Circuit



/ Pinning



PIN1 Emitter PIN 2 Collector PIN 3 Base

/ h_{FE} Classifications & Marking

h_{FE} Classifications Symbol	O	Y	GR
h_{FE} Range	80 160	120 240	200 400

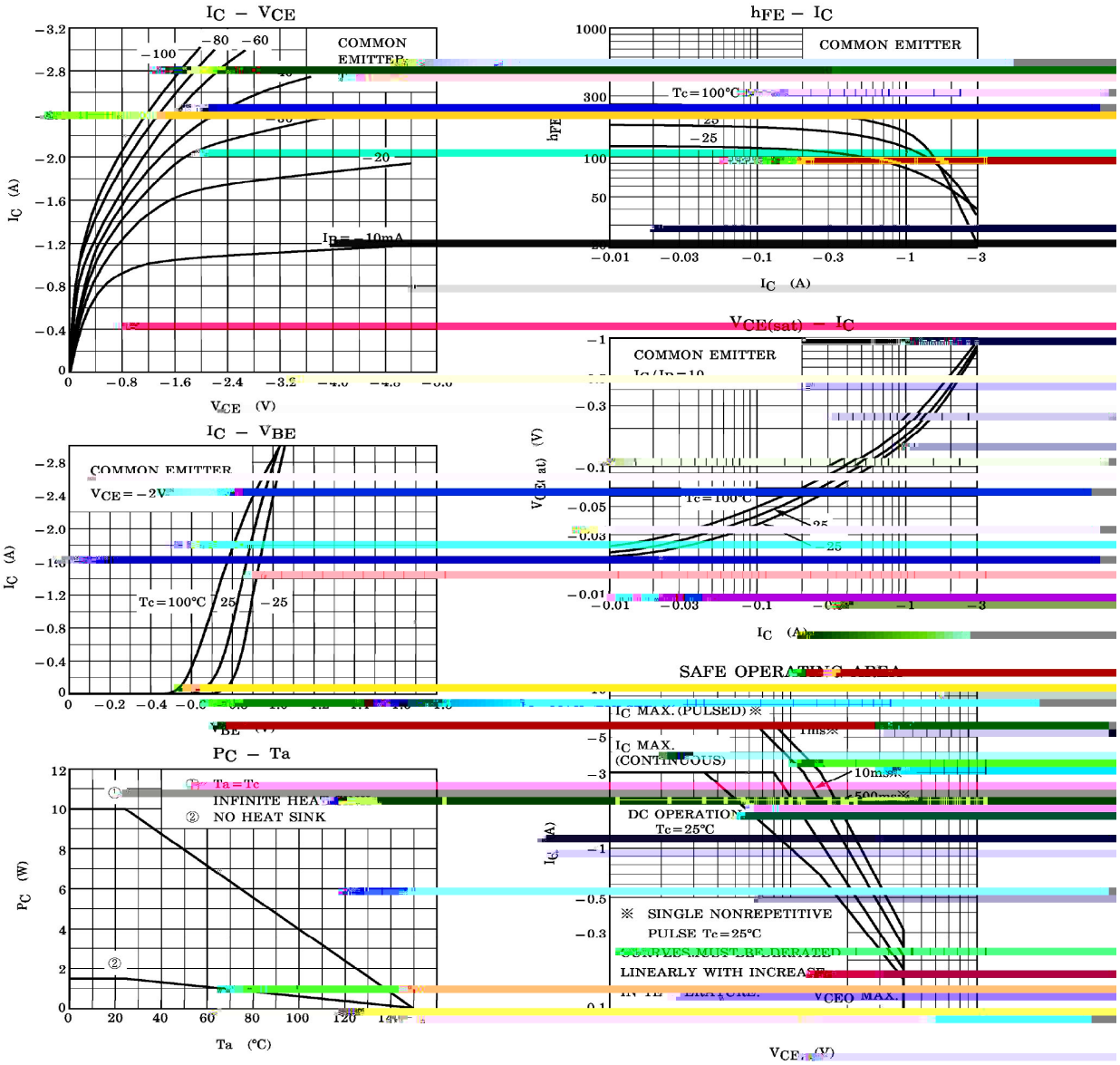
/ Absolute Maximum Ratings(Ta=25)

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-40	V
Collector to Emitter Voltage	V_{CEO}	-40	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-3.0	A
Base Current – Continuous	I_B	-1.0	A
Collector Power Dissipation	P_C	1.5	W
Collector Power Dissipation	P (T =25)	10	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

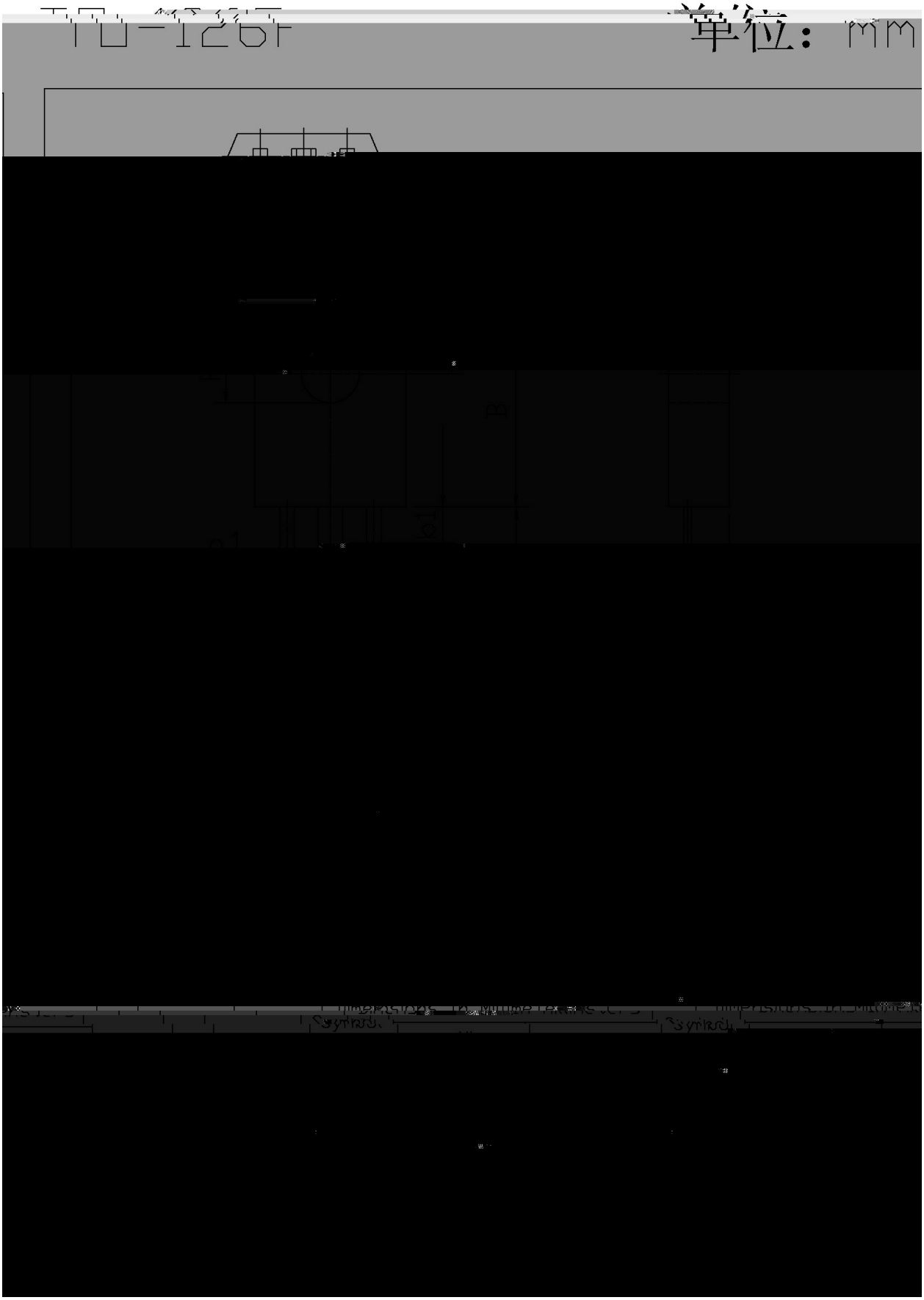
/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions		Min	Typ	Max	Unit
Collector Cut-Off Current	I_{CBO}	V_{CB}	$_E$=0				μA
Emitter Cut-Off Current	I_{EBO}	V_{EB}	$_C$=0			-0.1	μA
Collector to Emitter Breakdown	$_{CEO}$	I_C=-10mA	I_B=0	-40			
DC Current Gain	$_{FE(1)}$	V_{CE}	$_C$=-0.5A	80		400	
	$h_{FE(2)}$	V_{CE}	$_C$=-2.5A	25			
Voltage	$V_{CE(sat)}$	I_C=-2.0A	I_B=-0.2A			-0.8	V
Base to Emitter Voltage	V_{BE}	V_{CE}	$_C$=-0.5A			-1.0	V
Transition Frequency	f_T	V_{CE}	$_C$=-0.5A		100		MHz
Collector Output Capacitance	C_{ob}	V_{CB} f=1.0MHz	$_E$=0		35		pF

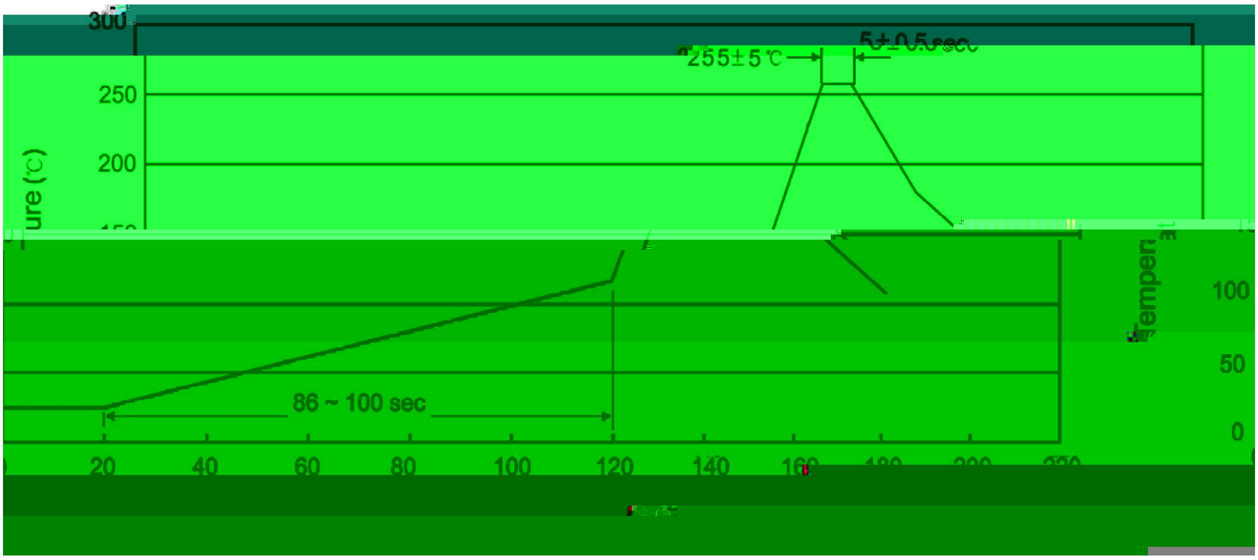
/ Electrical Characteristic Curve



/ Package Dimensions



(   ) / Temperature Profile for Dip Soldering(Pb-Free)



	Note:
1 25 150 60 90sec;	1.Preheating:25~150 , Time:60~90sec.
2 255±5 5±0.5sec;	2.Peak Temp.:255±5 , Duration:5±0.5sec.
3 2 10 /sec.	3. Cooling Speed: 2~10 /sec.

255±

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